# P-Channel 20-V (D-S) MOSFET

| PRODUCT SUMMARY     |                                     |                                 |                       |  |  |
|---------------------|-------------------------------------|---------------------------------|-----------------------|--|--|
| V <sub>DS</sub> (V) | R <sub>DS(on)</sub> (Ω)             | I <sub>D</sub> (A) <sup>a</sup> | Q <sub>g</sub> (Typ.) |  |  |
| - 20                | 0.0029 at V <sub>GS</sub> = - 10 V  | - 110                           | 120 nC                |  |  |
| - 20                | 0.0033 at V <sub>GS</sub> = - 4.5 V | - 90                            | 120110                |  |  |

**Bottom View** 

DFN5X6

- PIN1

Top View

#### **FEATURES**

- DT-Trench Power MOSFET
- 100 % R<sub>g</sub> Tested

#### **APPLICATIONS**

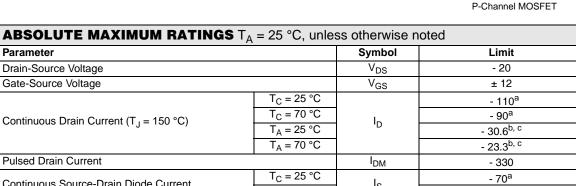
Notebook

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- Load Switch



Top View

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| Parameter  |                        | Symbol                            | Limit                  | Unit |
|--|------------------------|-----------------------------------|------------------------|------|
| Drain-Source Voltage   |                        | V <sub>DS</sub>                   | - 20                   | V    |
| Gate-Source Voltage  |                        | V <sub>GS</sub>                   | ± 12                   | v    |
|  | T <sub>C</sub> = 25 °C |                                   | - 110 <sup>a</sup>     |      |
| Continuous Drain Current (T <sub>.1</sub> = 150 °C)          | T <sub>C</sub> = 70 °C | I <sub>D</sub>                    | - 90 <sup>a</sup>      |      |
|  | T <sub>A</sub> = 25 °C | U                                 | - 30.6 <sup>b, c</sup> |      |
|  | T <sub>A</sub> = 70 °C |                                   | - 23.3 <sup>b, c</sup> | А    |
| Pulsed Drain Current   |                        | I <sub>DM</sub>                   | - 330                  | ~    |
| Continuous Source-Drain Diode Current                        | T <sub>C</sub> = 25 °C | I <sub>S</sub>                    | - 70 <sup>a</sup>      |      |
| Continuous Source-Drain Diode Current                        | T <sub>A</sub> = 25 °C | '8                                | - 56 <sup>b, c</sup>   |      |
| Single Pulse Avalanche Current                               | L = 0.1 mH             | I <sub>AS</sub>                   | - 60                   |      |
| Single Pulse Avalanche Energy                                | L = 0.1 mm             | E <sub>AS</sub>                   | 250                    | mJ   |
|  | T <sub>C</sub> = 25 °C |                                   | 170                    |      |
| Maximum Power Dissipation                                    | T <sub>C</sub> = 70 °C | P <sub>D</sub>                    | 83                     | w    |
|  | T <sub>A</sub> = 25 °C | ' D                               | 7.95 <sup>b, c</sup>   | ~~   |
|  | T <sub>A</sub> = 70 °C |                                   | 5.0 <sup>b, c</sup>    |      |
| Operating Junction and Storage Temperature Range             |                        | T <sub>J</sub> , T <sub>stg</sub> | - 55 to 150            | °C   |
| Soldering Recommendations (Peak Temperature) <sup>d, e</sup> |                        |                                   | 260                    |      |

| THERMAL RESISTANCE RATINGS                  |              |                   |         |         |      |
|---|--------------|-------------------|---------|---------|------|
| Parameter                                   |              | Symbol            | Typical | Maximum | Unit |
| Maximum Junction-to-Ambient <sup>b, f</sup> | t ≤ 10 s     | R <sub>thJA</sub> | 15      | 20      | °C/W |
| Maximum Junction-to-Case (Drain)            | Steady State | R <sub>thJC</sub> | 0.9     | 1.2     | 0/10 |

Notes:

a. Package limited.

b. Surface Mounted on 1" x 1" FR4 board.

c. t = 10 s.

d. The DFN5x6 is a leadless package. The end of the lead terminal is exposed

copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

e. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

f. Maximum under Steady State conditions is 54 °C/W.



Unit





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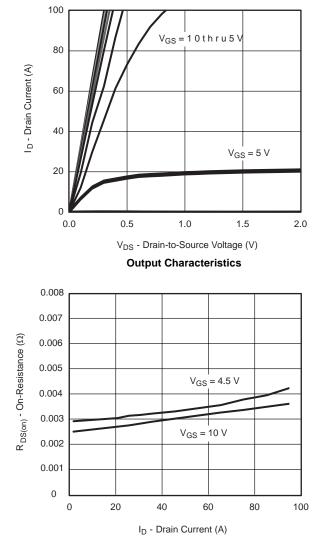
| Parameter                                     | Symbol                  | Test Conditions   | Min.  | Тур.   | Max.   | Unit   |  |
|---|-------------------------|---|-------|--------|--------|--------|--|
| Static  |                         |   |       |        |        |        |  |
| Drain-Source Breakdown Voltage                | V <sub>DS</sub>         | $V_{GS} = 0 V, I_{D} = -250 \mu A$  | - 20  |        |        | V      |  |
| V <sub>DS</sub> Temperature Coefficient       | $\Delta V_{DS}/T_{J}$   | ll = - 250 μA   |       | - 31   |        | m\//01 |  |
| V <sub>GS(th)</sub> Temperature Coefficient   | $\Delta V_{GS(th)}/T_J$ | i <sub>D</sub> = - 250 μA   |       | 6.5    |        | mV/°C  |  |
| Gate-Source Threshold Voltage                 | V <sub>GS(th)</sub>     | $V_{DS} = V_{GS}, I_{D} = -250 \ \mu A$   | - 0.3 |        | - 1.5  | V      |  |
| Gate-Source Leakage                           | I <sub>GSS</sub>        | $V_{DS} = 0 V, V_{GS} = \pm 12 V$   |       |        | ± 100  | nA     |  |
| Zana Cata Maltana Drain Current               | 1                       | V <sub>DS</sub> = - 20 V, V <sub>GS</sub> = 0 V                                       |       |        | - 1    |        |  |
| Zero Gate Voltage Drain Current               | IDSS                    | $V_{DS} = -20 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 55 \text{ °C}$ |       |        | - 10   | μA     |  |
| On-State Drain Current <sup>a</sup>           | I <sub>D(on)</sub>      | $V_{DS} = -5 V, V_{GS} = -10 V$   | - 350 |        |        | А      |  |
|   |                         | V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 20 A                                     |       | 0.0029 | 0.0032 | Ω      |  |
| Drain-Source On-State Resistance <sup>a</sup> | R <sub>DS(on)</sub>     | V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 15 A                                    |       | 0.0033 | 0.0037 |        |  |
| Forward Transconductance <sup>a</sup>         | 9 <sub>fs</sub>         | V <sub>DS</sub> = - 15 V, I <sub>D</sub> = - 20 A                                     |       | 93     |        | S      |  |
| Dynamic <sup>b</sup>                          |                         |   |       |        |        |        |  |
| Input Capacitance                             | C <sub>iss</sub>        |   |       | 12220  |        |        |  |
| Output Capacitance                            | C <sub>oss</sub>        | $V_{DS}$ = - 15 V, $V_{GS}$ = 0 V, f = 1 MHz  |       | 1931   |        | pF     |  |
| Reverse Transfer Capacitance                  | C <sub>rss</sub>        |   |       | 976    |        |        |  |
| Total Gate Charge                             | Qg                      | $V_{DS}$ = - 15 V, $V_{GS}$ = - 10 V, $I_{D}$ = - 20 A                                |       | 230    | 340    |        |  |
|   |                         |   |       | 78     | 140    | nC     |  |
| Gate-Source Charge                            | Q <sub>gs</sub>         | $V_{DS}$ = - 15 V, $V_{GS}$ = - 4.5 V, $I_{D}$ = - 20 A                               |       | 29     |        |        |  |
| Gate-Drain Charge                             | Q <sub>gd</sub>         |   |       | 37     |        |        |  |
| Gate Resistance                               | Rg                      | f = 1 MHz   |       | 2.9    |        | Ω      |  |
| Turn-On Delay Time                            | t <sub>d(on)</sub>      |   |       | 25     | 30     |        |  |
| Rise Time                                     | t <sub>r</sub>          | $V_{DD}$ = - 15 V, $R_L$ = 15 $\Omega$  |       | 15     | 30     | 1      |  |
| Turn-Off Delay Time                           | t <sub>d(off)</sub>     | $I_D \cong$ - 1.0 A, $V_{GEN}$ = - 10 V, $R_g$ = 1 $\Omega$                           |       | 110    | 170    |        |  |
| Fall Time                                     | t <sub>f</sub>          |   |       | 30     | 50     |        |  |
| Turn-On Delay Time                            | t <sub>d(on)</sub>      |   |       | 110    | 170    | ns     |  |
| Rise Time                                     | t <sub>r</sub>          | $V_{DD}$ = - 15 V, R <sub>L</sub> = 15 $\Omega$                                       |       | 100    | 150    |        |  |
| Turn-Off Delay Time                           | t <sub>d(off)</sub>     | $\rm I_D \cong$ - 1.0 A, $\rm V_{GEN}$ = - 4.5 V, $\rm R_g$ = 1 $\Omega$              |       | 100    | 150    |        |  |
| Fall Time                                     | t <sub>f</sub>          |   |       | 50     | 75     |        |  |
| Drain-Source Body Diode Characteristic        | cs                      |   |       |        | •      |        |  |
| Continuous Source-Drain Diode Current         | ا <sub>S</sub>          | T <sub>C</sub> = 25 °C  |       |        | 110    | ٨      |  |
| Pulse Diode Forward Current <sup>a</sup>      | I <sub>SM</sub>         |   |       |        | 370    | A      |  |
| Body Diode Voltage                            | V <sub>SD</sub>         | I <sub>S</sub> = - 5 A  |       | - 0.54 | - 1.1  | V      |  |
| Body Diode Reverse Recovery Time              | t <sub>rr</sub>         |   |       | 50     | 100    | ns     |  |
| Body Diode Reverse Recovery Charge            | Q <sub>rr</sub>         | I <sub>F</sub> = 3.5 A, dl/dt = 100 A/μs, T <sub>.1</sub> = 25 °C                     |       | 65     | 130    | nC     |  |
| Reverse Recovery Fall Time                    | t <sub>a</sub>          | $r_{\rm F} = 5.5$ A, unut = 100 A/µs, $r_{\rm J} = 25$ °C                             |       | 26     |        |        |  |
| Reverse Recovery Rise Time                    | t <sub>b</sub>          | -1 1  |       | 24     |        | ns     |  |

Notes:

a. Pulse test; pulse width  $\leq$  300  $\mu s,$  duty cycle  $\leq$  2 %. b. Guaranteed by design, not subject to production testing.

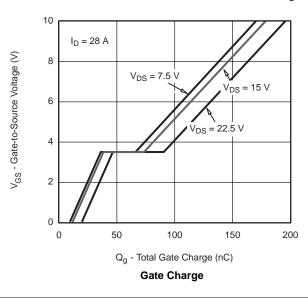
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

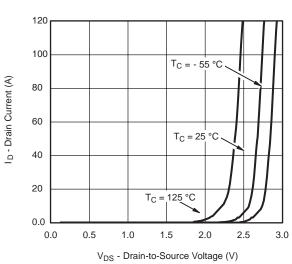




### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

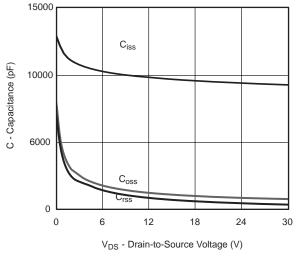




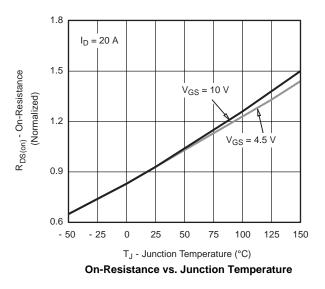


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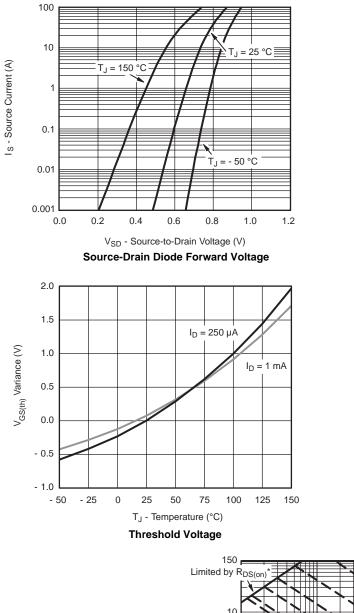
**Transfer Characteristics** 



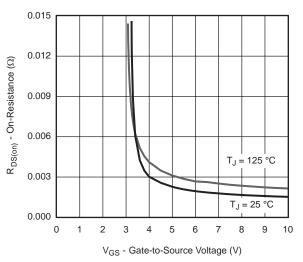
Capacitance



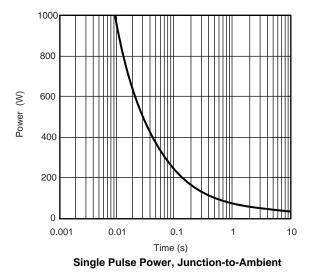


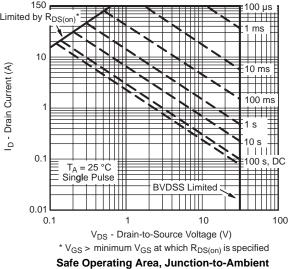


## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



On-Resistance vs. Gate-to-Source Voltage

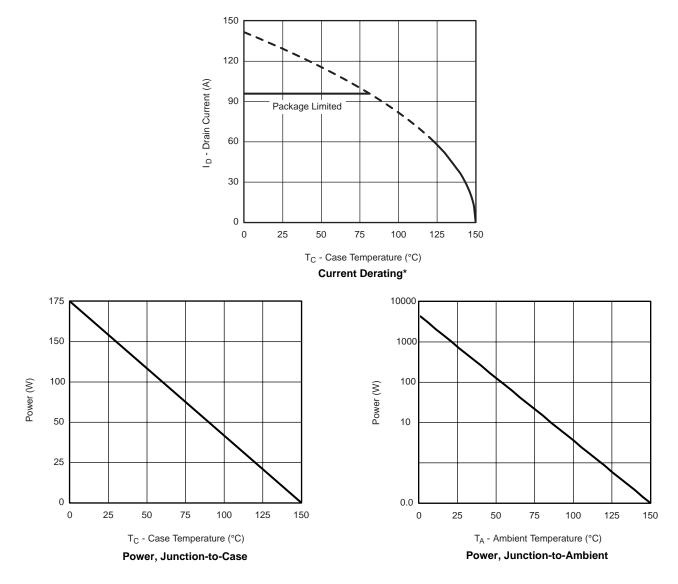






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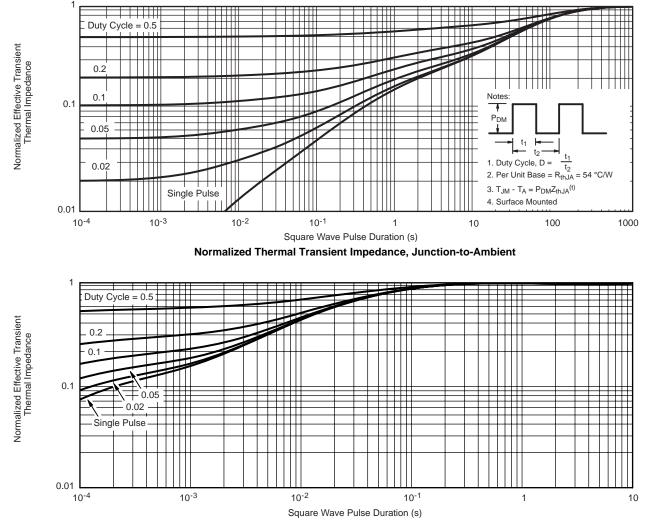


\* The power dissipation  $P_D$  is based on  $T_{J(max)}$  = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



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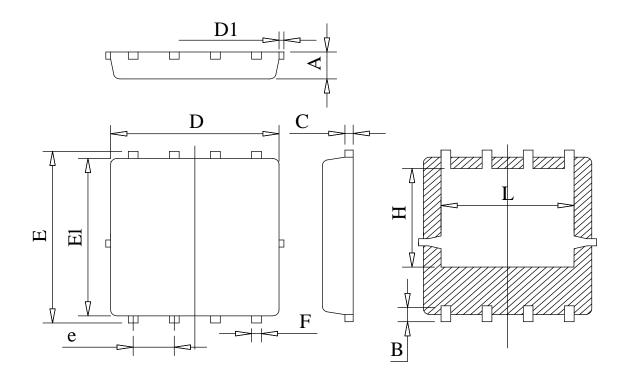


Normalized Thermal Transient Impedance, Junction-to-Case



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## DFN5X6-8L PACKAGE OUTLINE



## COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

| Unit : mm |      |       |      |
|-----------|------|-------|------|
| Symbol    | Min  | Тур   | Max  |
| A         | 0.78 | 0.95  | 1.12 |
| В         | 0.45 | 0.58  | 0.78 |
| С         | 0.18 | 0.254 | 0.36 |
| D         | 4.70 | 5.20  | 5.45 |
| D1        |      |       | 0.18 |
| Е         | 5.85 | 6.05  | 6.25 |
| E1        | 5.38 | 5.55  | 5.98 |
| e         | 1.15 | 1.27  | 1.40 |
| F         | 0.18 | 0.30  | 0.52 |
| Н         | 3.25 | 3.47  | 3.70 |
| L         | 3.75 | 4.00  | 4.25 |



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